

Vishay Semiconductors

RoHS

COMPLIANT

HALOGEN

FREE

Hyperfast Rectifier, 8 A FRED Pt®



2L TO-220 FullPAK

PRIMARY CHARACTERISTICS				
I _{F(AV)}	8 A			
V_{R}	600 V			
V _F at I _F	1.5 V			
t _{rr} (typ.)	14 ns			
T _J max.	175 °C			
Package	2L TO-220 FullPAK			
Circuit configuration	Single			

FEATURES

- Hyperfast recovery time, extremely low Q_{rr}
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		600	V
Average rectified forward current in DC	I _{F(AV)}	T _C = 105 °C	8	۸
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	80	A
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. N		MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	600	-	-	.,
Forward voltage V _F	I _F = 8 A	-	2.5	3.4	V	
	v _F	I _F = 8 A, T _J = 150 °C	-	1.5	2.0	
Reverse leakage current I _R		$V_R = V_R$ rated	-	0.02	30	
		T _J = 150 °C, V _R = V _R rated	-	21	150	μA
Junction capacitance	C _T	V _R = 600 V - 6 -		-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8 -		nH		





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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	14	18	ns
Povorco rocovory timo		I _F = 8 A, dI _F /dt = 100 A/μs, V _R = 30 V		-	15	24	
Reverse recovery time t _{rr}	T _J = 25 °C		-	17	-		
		T _J = 125 °C	$I_F = 8 \text{ A},$ $dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_B = 390 \text{ V}$	-	33	-	
Peak recovery current I _{RRM}		T _J = 25 °C		-	2.6	-	Α
	IRRM	T _J = 125 °C		-	4.3	-	
Daylaraa waaayaw aharaa	0	T _J = 25 °C		-	22	-	nC
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	77	-	IIC
Reverse recovery time	t _{rr}	T _J = 125 °C	$I_F = 8 \text{ A},$ $dI_F/dt = 600 \text{ A/}\mu\text{s},$ $V_R = 390 \text{ V}$	-	26	-	ns
Peak recovery current	I _{RRM}			-	11	-	Α
Reverse recovery charge	Q _{rr}			-	150	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	IBOL TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction-to-case	R _{thJC}		-	4.6	5.5	
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount	-	-	70	°C/W
Typical thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	=	0.5	-	
Weight			-	2	-	g
weignt			-	0.07	-	OZ.
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style 2L TO-220 FullPAK		ETX08	306FP	



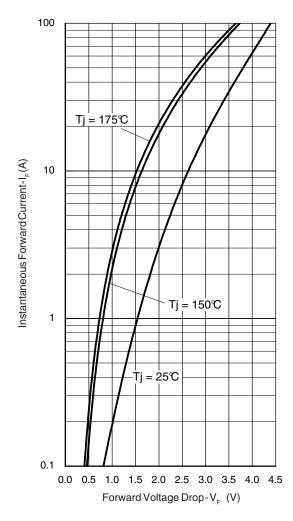


Fig. 1 - Typical Forward Voltage Drop Characteristics

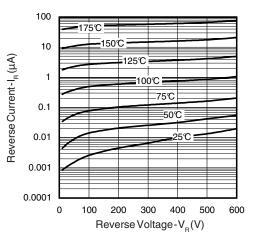


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

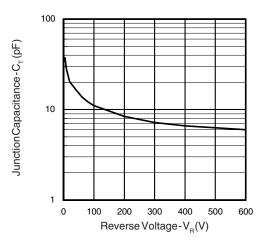


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

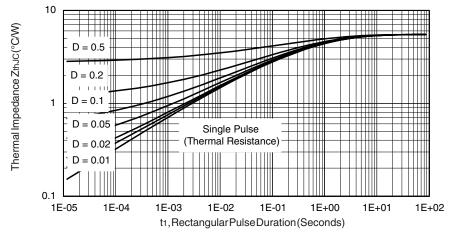


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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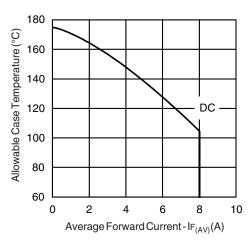


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

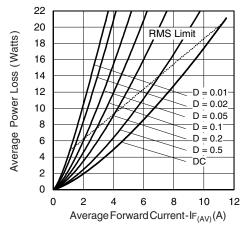


Fig. 6 - Forward Power Loss Characteristics

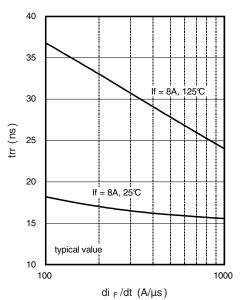


Fig. 7 - Typical Reverse Recovery vs. dl_F/dt

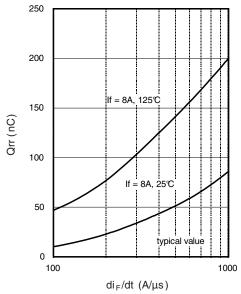
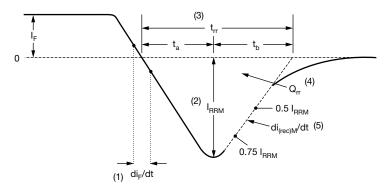


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{rr}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\rm Q_{rr}$ area under curve defined by $\rm t_{rr}$ and $\rm I_{RRM}$

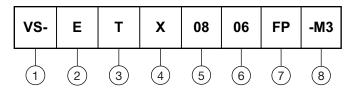
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Circuit configuration:

E = single

3 - T = TO-220

4 - X = hyperfast recovery time

5 - Current code: 08 = 8 A

Voltage code: 06 = 600 V

7 - FP = 2L TO-220 FullPAK

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-ETX0806FP-M3	50	1000	Antistatic plastic tube		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96157			
Part marking information	www.vishay.com/doc?95392			



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